



TO-92 Plastic-Encapsulate Transistors

2N5551 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

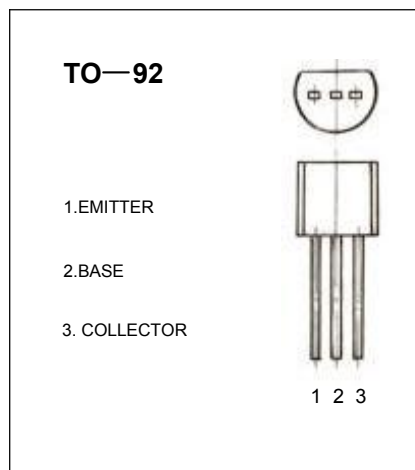
I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 180 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1 mA, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=120 V, I_E=0$			50	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4 V, I_C=0$			50	μA
DC current gain	$H_{FE(1)}$	$V_{CE}=5V, I_C=1mA$	80			
DC current gain	$H_{FE(2)}$	$V_{CE}=5V, I_C=10mA$	80		300	
DC current gain	$H_{FE(3)}$	$V_{CE}=5V, I_C=50mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$ $f=100MHz$	100		300	MHz

CLASSIFICATION OF HFE

Rank	1	2	3
Range	100-150	150-200	200-300